

2SA952 PNP Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into three group, M, L and K according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	30	V
Collector Emitter Voltage	$-V_{CEO}$	25	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	700	mA
Base Current	$-I_B$	150	mA
Power Dissipation	P_{tot}	600	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 1 \text{ V}$, $-I_C = 100 \text{ mA}$	h_{FE}	90	180	-
Current Gain Group M	h_{FE}	135	270	-
L	h_{FE}	200	400	-
K	h_{FE}	50	-	-
at $-V_{CE} = 1 \text{ V}$, $-I_C = 700 \text{ mA}$				
Collector Base Cutoff Current at $-V_{CB} = 30 \text{ V}$	$-I_{CBO}$	-	100	nA
Emitter Base Cutoff Current at $-V_{EB} = 5 \text{ V}$	$-I_{EBO}$	-	100	nA
Collector Emitter Saturation Voltage at $-I_C = 700 \text{ mA}$, $-I_B = 70 \text{ mA}$	$-V_{CE(sat)}$	-	0.6	V
Base Emitter Saturation Voltage at $-I_C = 700 \text{ mA}$, $-I_B = 70 \text{ mA}$	$-V_{BE(sat)}$	-	1.2	V
Base Emitter Voltage at $-V_{CE} = 6 \text{ V}$, $-I_C = 10 \text{ mA}$	$-V_{BE}$	0.6	0.7	V
Gain Bandwidth Product at $-V_{CE} = 6 \text{ V}$, $-I_E = 10 \text{ mA}$	f_T	50	-	MHz
Collector to Base Capacitance at $-V_{CB} = 6 \text{ V}$, $f = 1 \text{ MHz}$	C_{OB}	-	40	pF

